



S8550M (3CG8550M)

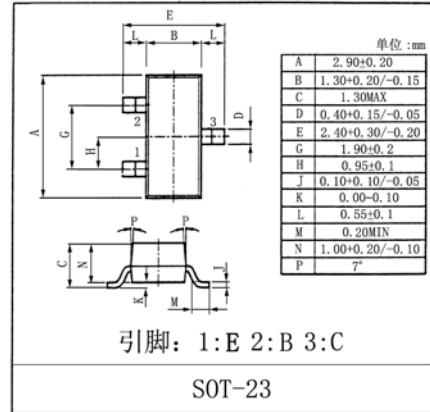
硅 PNP 半导体三极管/SILICON PNP TRANSISTOR

用途:用于功率放大电路。/Purpose: Power amplifier applications.

特点:与 S8050M(3DG8050M) 互补。/Features: Complementary pair with S8050M(3DG8050M).

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CBO}	-40	V
V _{CEO}	-25	V
V _{EBO}	-6.0	V
I _C	-800	mA
I _B	-200	mA
P _C	450	mW
T _j	150	℃
T _{stg}	-65~150	℃



电性能参数/Electrical characteristics(Ta=25℃)

参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CBO}	I _C =-0.1mA I _E =0	-40			V
V _{CEO}	I _C =-2.0mA I _B =0	-25			V
V _{EBO}	I _E =-0.1mA I _C =0	-6.0			V
I _{CBO}	V _{CB} =-35V I _E =0			-0.1	μA
I _{EBO}	V _{EB} =-6.0V I _C =0			-0.1	μA
h _{FE(1)}	V _{CE} =-1.0V I _C =-100mA	85		300	
h _{FE(2)}	V _{CE} =-1.0V I _C =-500mA	40			
h _{FE(3)}	V _{CE} =-1.0V I _C =-5.0mA	45			
V _{CE(sat)}	I _C =-500mA I _B =-50mA		-0.28	-0.6	V
V _{BE(sat)}	I _C =-500mA I _B =-50mA		-0.98	-1.2	V
V _{BE}	V _{CE} =-1.0V I _C =-10mA		-0.66	-1.0	V
f _T	V _{CE} =-10V I _C =-50mA	100	200		MHz
C _{ob}	V _{CB} =-10V I _E =0 f=1.0MHz		15		pF

h_{FE(1)} 分档、印章/h_{FE(1)} classifications、Marking:

h _{FE(1)} 分档 h _{FE(1)} Classifications	B	C	D
h _{FE(1)} 范围 h _{FE(1)} Range	85~160	120~200	160~300
印章 Marking	HY4B	HY4C	HY4D



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